



Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)				
30	0.022 at V _{GS} = 10 V	10				
	0.030 at V _{GS} = 4.5 V	8.5				

SCHOTTKY PRODUCT SUMMARY							
	V _{SD} (V)						
V _{DS} (V)	Diode Forward Voltage	I _F (A)					
30	0.50 V at 1.0 A	3.0					

FEATURES

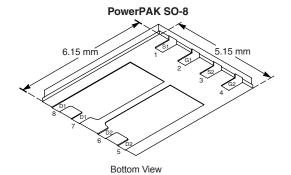
- Halogen-free According to IEC 61249-2-21 Available
- LITTLE FOOT[®] Plus Schottky
- New Low Thermal Resistance PowerPAK[®]
 Package with Low 1.07 mm Profile
- 100 % R_q Tested

Pb-free RoHS



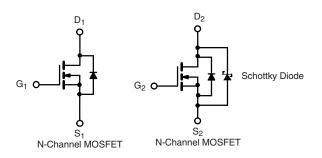
APPLICATIONS

• Bus and Logic DC-DC



Ordering Information: Si7842DP-T1-E3 (Lead (Pb)-free)

Si7842DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted								
Parameter	Symbol	10 s	10 s Steady State					
Drain-Source Voltage		V_{DS}	3	v				
Gate-Source Voltage		V_{GS}	±					
Continuous Drain Current /T _ 150 °C)a	T _A = 25 °C	I _D	10	6.3				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		6.0	5.0	Α .			
Pulsed Drain Current		I _{DM}	3					
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.1				
Maximum Dawar Dissination	T _A = 25 °C	P _D	3.5	1.4	W			
Maximum Power Dissipation ^a	T _A = 70 °C	'b	2.2	0.9	vv			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150					
Soldering Recommendations (Peak Temperature) ^{b,c}			2	60	- °C			

THERMAL RESISTANCE RATINGS									
Parameter			MOSFET		Schottky				
		Symbol	Typical	Maximum	Typical	Maximum	Unit		
Marrian na lunation to Ambient	t ≤ 10 s	R _{thJA}	26	35	26	35			
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	60	85	60	85	°C/W		
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	3.9	5.5	3.9	5.5			

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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SPECIFICATIONS $T_J = 25$	°C, unles	ss otherwise noted					
Parameter	Symbol	Test Condition	Min.	Typ. ^b	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		0.8		2.4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$				± 100	nA
		V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	
Zero Gate Voltage Drain Current	I _{DSS}	VDS = 30 V, VGS = 0 V	Ch-2			100	пΔ
Zero date voltage Drain Gurrent	יטאא	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			15	<u>μ</u> Α
			Ch-2			2000	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$		20			Α
Drain-Source On-State Resistance ^a	В	$V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$		0.018 0.		0.022	0
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 6.5 A 0.024				0.030	Ω
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 7.5 \text{ A}$	V _{DS} = 15 V, I _D = 7.5 A		22		S
	V	1 1 4 3 4 9 3 4	Ch-1		0.8	1.2	V
Diode Forward Voltage ^a	V _{SD}	$I_S = 1 A, V_{GS} = 0 V$	Ch-2		0.47	0.5	V
Dynamic ^b							
Total Gate Charge	Qg				13	20	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.5$	A		2		nC
Gate-Drain Charge	Q_{gd}				2.7		
Gate Resistance	R_g			0.5	1.2	3.2	Ω
Turn-On Delay Time	t _{d(on)}				8	16	
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω			10	20	ns
Turn-Off Delay Time	t _{d(off)}				21	40	
Fall Time	t _f				10	20	
Source-Drain Reverse Recovery	very , ,	I _F = 1.7 A, dI/dt = 100 A/μs	Ch-1		40	80	
Time	t _{rr}	F = 1.7 A, α//αt = 100 A/μs Ch-2			32	70	

Notes: a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

SCHOTTKY SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted								
Parameter	Symbol	Test Condition	Min. Typ. N			Unit		
Forward Voltage Drop	V _F	I _F = 1.0 A		0.47	0.50	V		
		I _F = 1.0 A, T _J = 125 °C		0.36	0.42			
Maximum Reverse Leakage Current	I _{rm}	V _r = 30 V		0.004	0.100	mA		
		V _r = 30 V, T _J = 100 °C		0.7	10			
		$V_r = -30 \text{ V}, T_J = 125 ^{\circ}\text{C}$		3.0	20			
Junction Capacitance	C _T	V _r = 10 V		50		pF		

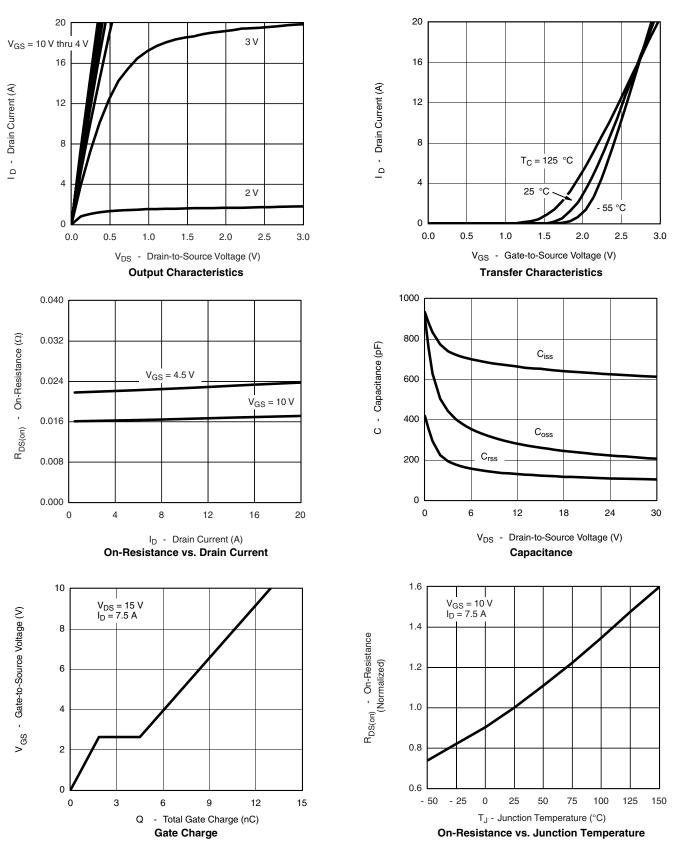
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.







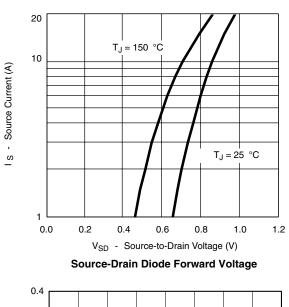
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

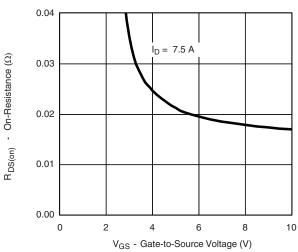


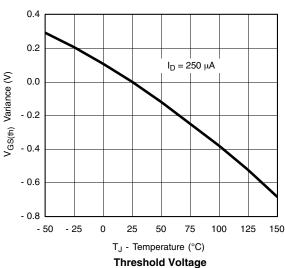
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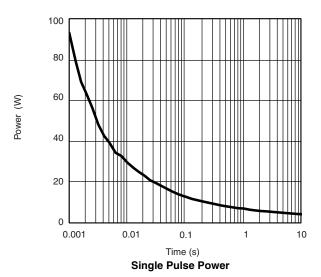
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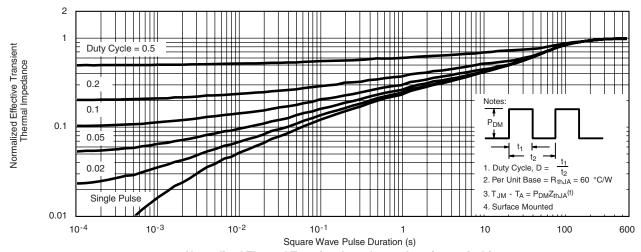






On-Resistance vs. Gate-to-Source Voltage

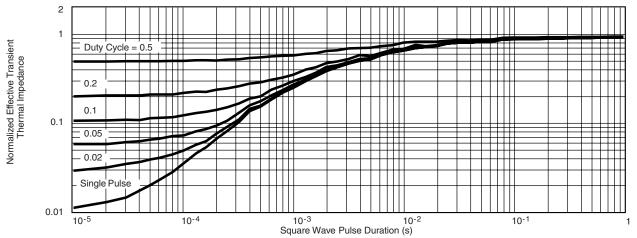




Normalized Thermal Transient Impedance, Junction-to-Ambient



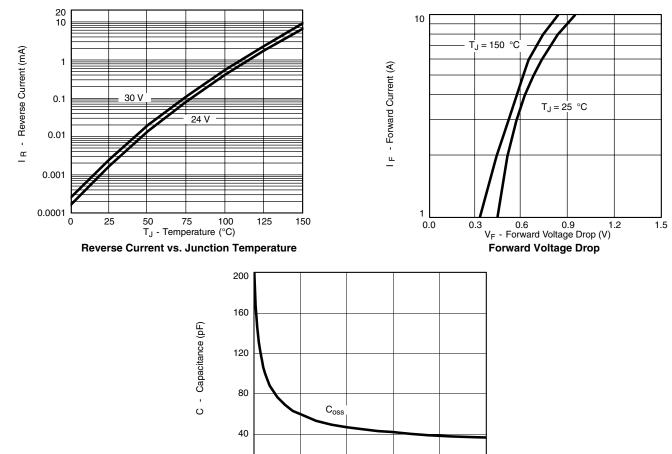
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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 V_{DS} -

12 18 24 Drain-to-Source Voltage (V)

Capacitance



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